



G. Device & Process Modeling, Simulation and Reliability 분과

2021년 1월 28일(목), 09:00-10:30 / 채널 D

[TD1-G] Ab Initio Simulation and Quantum Transport

좌장: 김성호 교수 (세종대학교), 장지원 교수 (UNIST)

TD1-G-1 09:00-09:15	A Full-stack Modeling Study on Si-base Controlled-NOT Quantum Logic Gate Devices: Exploring the Fidelity of Entangled Computations Hoon Ryu, Junghee Ryu, and Ji-Hoon Kang <i>KISTI</i>
TD1-G-2 09:15-09:30	First-principles Study of Lateral WSe₂ p-n Junction Tae Hyung Kim, Juho Lee, Jun Seong Lee, and Yong-Hoon Kim <i>School of Electrical Engineering, KAIST</i>
TD1-G-3 09:30-09:45	Non-Equilibrium Green's Function Simulation of Nanosheet MOSFETs with Various Cross-sections Phil-Hun Ahn and Sung-Min Hong <i>School of Electrical Engineering and Computer Science, GIST</i>
TD1-G-4 09:45-10:00	First-Principles Study of Vertical Van der Waals Heterojunction-Based Tunnel Field-Effect Transistors Juho Lee and Yong-Hoon Kim <i>School of Electrical Engineering, KAIST</i>
TD1-G-5 10:00-10:15	Quantum Transport Simulation on Ferroelectric Tunnel Junctions with 2D Layered Ferroelectric CuInP₂S₆ Eunyeong Yang and Jiwon Chang <i>School of Electrical and Computer Engineering, UNIST</i>
TD1-G-6 10:15-10:30	First-principles Study of the MXene-electrode Based Molecular Junctions Hyeonwoo Yeo, Juho Lee, and Yong-Hoon Kim <i>School of Electrical Engineering, KAIST</i>